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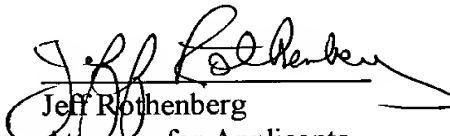
production of additional n-doped and/or p-doped areas in the p-doped or n-doped inner area and in the fringe area of the n-doped or the p-doped trough that form the structure of the semiconductor component.

REMARKS

By this Preliminary Amendment, claim 1 is being amended to conform with the Article 19 Amendment filed in the international proceedings of the corresponding PCT application.

Applicant respectfully requests that claim 1 as amended herein, claims 4, 7, 15, 22, 25 and 26 as amended in the Preliminary Amendment submitted March 27, 2001, and original claims 2, 3, 5, 6, 8-14, 16-21, 23, 24 and 27 be the subject of U.S. national phase examination.

Respectfully submitted,


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Dated: June 27, 2001

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Version With Markings to Show Changes Made

1. (Amended) A method for producing integrable semiconductor components, in particular transistors, diodes, and logic gates, starting with a p-doped or n-doped semiconductor substrate in the following steps:

application of a mask onto the semiconductor substrate for definition of a window delimited by a peripheral edge;

production of an n-doped trough in the p-doped semiconductor substrate or p-doped trough in the n-doped semiconductor substrate by means of ion implantation through the mask using an energy that will assure that a p-doped or an n-doped inner area remains on [the] a surface of the semiconductor substrate, whereby [the] a fringe area of the n-doped or p-doped trough extends up to the surface of the semiconductor substrate [or creation of an n-doped or p-doped area that extends up to the surface of the semiconductor substrate by using ion implantation through the mask, whereby p-doping or n-doping is inserted into the n-doped area or into the p-doped area such that a p-doped or n-doped inner area is created in the n-doped area or in the p-doped area and is enclosed by the n-doped or p-doped area]; and

production of additional n-doped and/or p-doped areas in the p-doped or n-doped inner area and in the fringe [are] area of the n-doped or the p-doped trough that form the structure of the semiconductor component.